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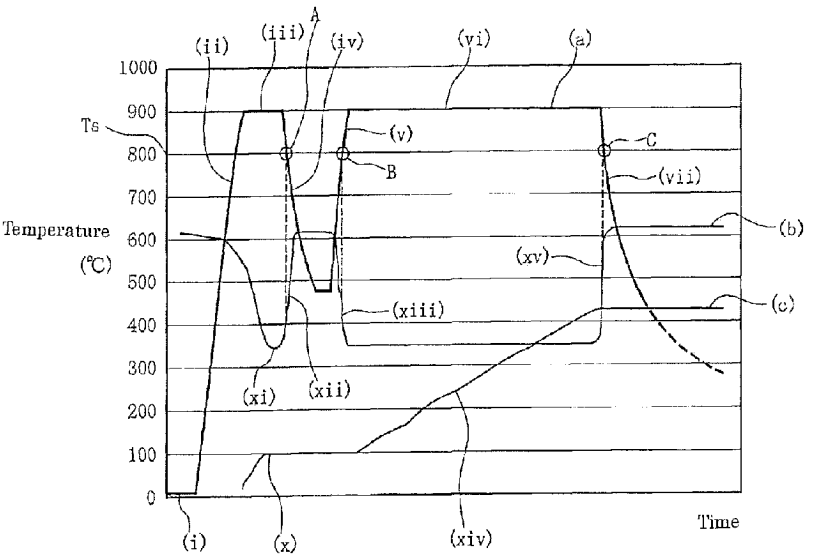
(54) **Titre : PROCEDE ET DISPOSITIF POUR MESURER LA TEMPERATURE PENDANT LE DEPOT DE SEMI-CONDUCTEUR**
(54) **Title: METHOD AND DEVICE FOR MEASURING TEMPERATURE DURING DEPOSITION OF SEMICONDUCTOR**




(57) **Abrégé/Abstract:**
Provided is a method and a device for measuring a temperature which can recognize the temperature of a semiconductor layer directly with high precision when the semiconductor layer is formed by deposition. The quantity of laser light transmitted a semiconductor layer is monitored by a photodetector by using laser light having a wavelength λs at which the transmittance of light changes abruptly when the temperature of the semiconductor layer reaches Ts during or after deposition. When heat being given to the semiconductor layer is changed, the quantity of laser light monitored by the photodetector changes abruptly when the temperature of the semiconductor layer reaches Ts at a time A, B or C. Consequently, the fact that the temperature of the semiconductor layer reached Ts at a time A, B or C can be recognized exactly, and an error in temperature information observed by a device for measuring temperature variations can be calibrated, for example.